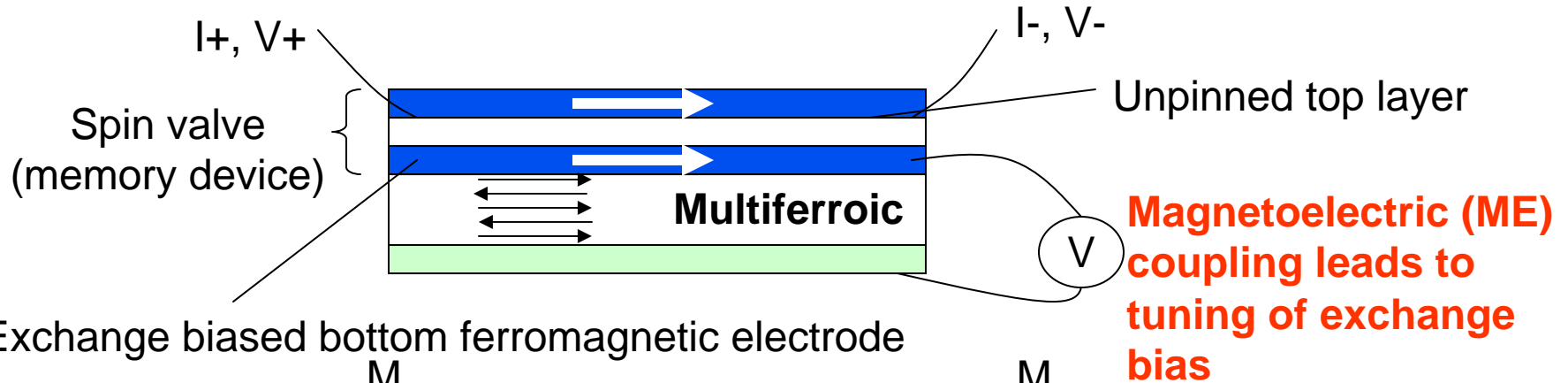
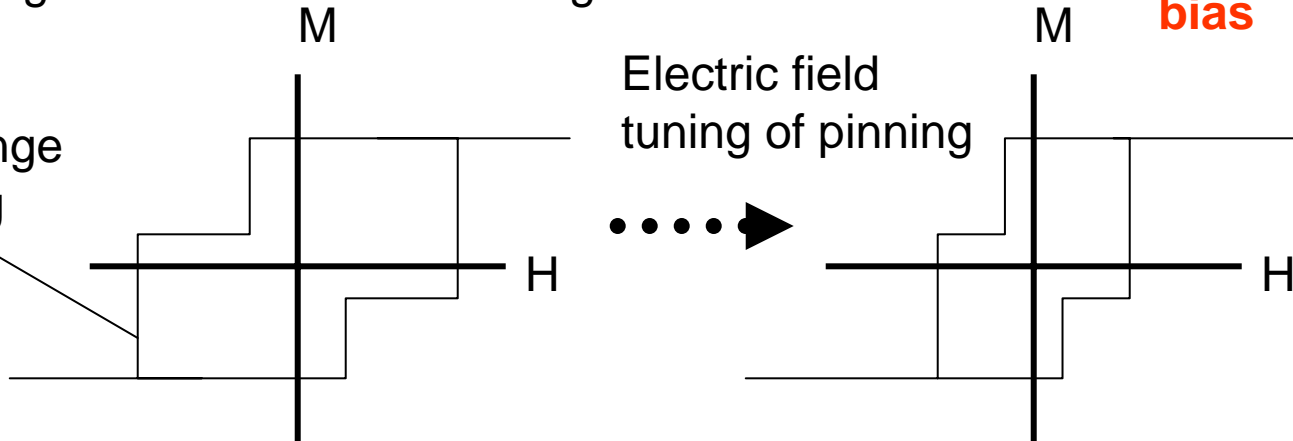


Novel multiferroic thin film memory devices

Electric-field tunable spin valves are being investigated



Exchange pinning



Exchange bias at ferromagnet/multiferroic interfaces has been studied for various thin film and bulk multiferroics including BiFeO_3 , TbMnO_3 , LuMnO_3 , and Cr_2O_3 . Tunable spin valve structures have been made. Magnetoresistance devices using BiFeO_3 as the exchange biasing layer have been demonstrated.

